

Gilberto Medeiros-Ribeiro

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

164
papers

11,264
citations

56
h-index

104
g-index

173
ext. papers

12,140
ext. citations

5.5
avg, IF

5.89
L-index

#	Paper	IF	Citations
164	Raman spectra of twisted bilayer graphene close to the magic angle. <i>2D Materials</i> , 2022 , 9, 025007	5.9	3
163	Prediction-free, real-time flexible control of tidal lagoons through Proximal Policy Optimisation: A case study for the Swansea Lagoon. <i>Ocean Engineering</i> , 2022 , 247, 110657	3.9	0
162	The limits of near field immersion microwave microscopy evaluated by imaging bilayer graphene moiré patterns. <i>Nature Communications</i> , 2021 , 12, 2980	17.4	5
161	Twisted Bilayer Graphene: A Versatile Fabrication Method and the Detection of Variable Nanometric Strain Caused by Twist-Angle Disorder. <i>ACS Applied Nano Materials</i> , 2021 , 4, 1858-1866	5.6	7
160	Localization of lattice dynamics in low-angle twisted bilayer graphene. <i>Nature</i> , 2021 , 590, 405-409	50.4	46
159	Observation of moiré superlattices on twisted bilayer graphene by scanning microwave impedance microscopy 2020 ,		2
158	Assessing electronic states of InAsP/GaAs self-assembled quantum dots by photoluminescence and modulation spectroscopy. <i>Journal of Luminescence</i> , 2019 , 206, 639-644	3.8	1
157	Quantum corrections to conductivity in graphene with vacancies. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2018 , 100, 40-44	3	7
156	Quasistatic and Pulse Measuring Techniques 2016 , 341-362		1
155	Quantized conductance coincides with state instability and excess noise in tantalum oxide memristors. <i>Nature Communications</i> , 2016 , 7, 11142	17.4	69
154	Patterning graphene with a helium ion microscope: Observation of metal-insulator transition induced by disorder. <i>Physical Review B</i> , 2015 , 91,	3.3	7
153	Graphene nanoribbon superlattices fabricated via He ion lithography. <i>Applied Physics Letters</i> , 2014 , 104, 193114	3.4	29
152	Oxide Based Memristive Nanodevices 2014 , 219-256		1
151	A scalable neuristor built with Mott memristors. <i>Nature Materials</i> , 2013 , 12, 114-7	27	614
150	State Dynamics and Modeling of Tantalum Oxide Memristors. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 2194-2202	2.9	120
149	Band offsets in transition-metal oxide heterostructures. <i>Journal Physics D: Applied Physics</i> , 2013 , 46, 295303		10
148	Characterization of electroforming-free titanium dioxide memristors. <i>Beilstein Journal of Nanotechnology</i> , 2013 , 4, 467-73	3	54

147	AC sense technique for memristor crossbar. <i>Electronics Letters</i> , 2012 , 48, 757	1.1	23
146	Nitride memristors. <i>Applied Physics A: Materials Science and Processing</i> , 2012 , 109, 1-4	2.6	58
145	Engineering nonlinearity into memristors for passive crossbar applications. <i>Applied Physics Letters</i> , 2012 , 100, 113501	3.4	162
144	Continuous electrical tuning of the chemical composition of TaO(x)-based memristors. <i>ACS Nano</i> , 2012 , 6, 2312-8	16.7	100
143	Intermixing during Ripening in GeBi Incoherent Epitaxial Nanocrystals. <i>Journal of Physical Chemistry C</i> , 2012 , 116, 901-907	3.8	4
142	Designing memristors: Physics, materials science and engineering 2012 ,		1
141	Electronic structure and transport measurements of amorphous transition-metal oxides: observation of Fermi glass behavior. <i>Applied Physics A: Materials Science and Processing</i> , 2012 , 107, 1-11	2.6	47
140	Measuring the switching dynamics and energy efficiency of tantalum oxide memristors. <i>Nanotechnology</i> , 2011 , 22, 505402	3.4	85
139	Sub-nanosecond switching of a tantalum oxide memristor. <i>Nanotechnology</i> , 2011 , 22, 485203	3.4	506
138	Dopant Control by Atomic Layer Deposition in Oxide Films for Memristive Switches. <i>Chemistry of Materials</i> , 2011 , 23, 123-125	9.6	56
137	Two- and Three-Terminal Resistive Switches: Nanometer-Scale Memristors and Memistors. <i>Advanced Functional Materials</i> , 2011 , 21, 2660-2665	15.6	64
136	Sketched oxide single-electron transistor. <i>Nature Nanotechnology</i> , 2011 , 6, 343-7	28.7	103
135	The switching location of a bipolar memristor: chemical, thermal and structural mapping. <i>Nanotechnology</i> , 2011 , 22, 254015	3.4	82
134	Metal/TiO ₂ interfaces for memristive switches. <i>Applied Physics A: Materials Science and Processing</i> , 2011 , 102, 785-789	2.6	128
133	Feedback write scheme for memristive switching devices. <i>Applied Physics A: Materials Science and Processing</i> , 2011 , 102, 973-982	2.6	63
132	Coexistence of memristance and negative differential resistance in a nanoscale metal-oxide-metal system. <i>Advanced Materials</i> , 2011 , 23, 1730-3	24	91
131	Anatomy of a nanoscale conduction channel reveals the mechanism of a high-performance memristor. <i>Advanced Materials</i> , 2011 , 23, 5633-40	24	338
130	Spectromicroscopy of tantalum oxide memristors. <i>Applied Physics Letters</i> , 2011 , 98, 242114	3.4	77

129	Progress in CMOS-memristor integration 2011 ,		6
128	Lognormal switching times for titanium dioxide bipolar memristors: origin and resolution. <i>Nanotechnology</i> , 2011 , 22, 095702	3.4	61
127	X-RAY DIFFRACTION METHODS FOR STUDYING STRAIN AND COMPOSITION IN EPITAXIAL NANOSTRUCTURED SYSTEMS. <i>Materials and Energy</i> , 2011 , 211-279		4
126	Impact of geometry on the performance of memristive nanodevices. <i>Nanotechnology</i> , 2011 , 22, 254026	3.4	22
125	Nanoscale lateral switchable rectifiers fabricated by local anodic oxidation. <i>Journal of Applied Physics</i> , 2011 , 110, 024511	2.5	14
124	Observation of two resistance switching modes in TiO ₂ memristive devices electroformed at low current. <i>Nanotechnology</i> , 2011 , 22, 254007	3.4	62
123	Hybrid CMOS/memristor circuits 2010 ,		39
122	A memristor-based nonvolatile latch circuit. <i>Nanotechnology</i> , 2010 , 21, 235203	3.4	56
121	Atomic ordering dependence on growth method in Ge:Si(001) islands: Influence of surface kinetic and thermodynamic interdiffusion mechanisms. <i>Physical Review B</i> , 2010 , 82,	3.3	18
120	High switching endurance in TaO _x memristive devices. <i>Applied Physics Letters</i> , 2010 , 97, 232102	3.4	467
119	Novel Approach for High-Resolution Elastic Behavior Assessment of Alloyed Strained Nanostructures. <i>Journal of Physical Chemistry C</i> , 2010 , 114, 12409-12415	3.8	3
118	Morphological and electrical changes in TiO ₂ memristive devices induced by electroforming and switching. <i>Physica Status Solidi - Rapid Research Letters</i> , 2010 , 4, 16-18	2.5	59
117	Direct identification of the conducting channels in a functioning memristive device. <i>Advanced Materials</i> , 2010 , 22, 3573-7	24	278
116	Diffusion of adhesion layer metals controls nanoscale memristive switching. <i>Advanced Materials</i> , 2010 , 22, 4034-8	24	95
115	Microstrip resonators for electron paramagnetic resonance experiments. <i>Review of Scientific Instruments</i> , 2009 , 80, 075111	1.7	23
114	Structural and chemical characterization of TiO ₂ memristive devices by spatially-resolved NEXAFS. <i>Nanotechnology</i> , 2009 , 20, 485701	3.4	52
113	Submicron fabrication by local anodic oxidation of germanium thin films. <i>Nanotechnology</i> , 2009 , 20, 345301	3.4	8
112	Probing microwave capacitance of self-assembled quantum dots. <i>Applied Physics Letters</i> , 2009 , 95, 032103	3.4	34

111	Chemical Nano-tomography of Self-assembled Ge-Si:Si(001) Islands from Quantitative High Resolution Transmission Electron Microscopy. <i>Materials Research Society Symposia Proceedings</i> , 2009 , 1184, 111		
110	Memristor-CMOS hybrid integrated circuits for reconfigurable logic. <i>Nano Letters</i> , 2009 , 9, 3640-5	11.5	507
109	Extended excitons and compact heliumlike biexcitons in type-II quantum dots. <i>Physical Review B</i> , 2009 , 80,	3.3	29
108	Identification of two light-induced charge states of the oxygen vacancy in single-crystalline rutile TiO ₂ . <i>Physical Review B</i> , 2009 , 80,	3.3	44
107	Control of Ge/Si intermixing during Ge island growth. <i>Applied Physics Letters</i> , 2009 , 94, 053118	3.4	12
106	Revealing Quantitative 3D Chemical Arrangement on GeBi Nanostructures. <i>Journal of Physical Chemistry C</i> , 2009 , 113, 9018-9022	3.8	16
105	Evolution of thermodynamic potentials in closed and open nanocrystalline systems: Ge-Si:Si(001) islands. <i>Physical Review Letters</i> , 2008 , 100, 226101	7.4	41
104	Scanning tunneling microscopy of template-stripped Au surfaces and highly ordered self-assembled monolayers. <i>Langmuir</i> , 2008 , 24, 5984-7	4	16
103	Reactive epitaxy of metallic hafnium silicide nanocrystals. <i>Applied Physics Letters</i> , 2008 , 93, 013107	3.4	2
102	Determination of spin polarization in InAsGaAs self-assembled quantum dots. <i>Applied Physics Letters</i> , 2008 , 92, 132106	3.4	2
101	Two-dimensional magnetoexcitons in type-II semiconductor quantum dots. <i>Physical Review B</i> , 2008 , 78,	3.3	15
100	Thermodynamics of coherently-strained Ge _x Si _{1-x} nanocrystals on Si(001): alloy composition and island formation. <i>Nano Letters</i> , 2007 , 7, 223-6	11.5	68
99	Technical Report: Industrial Research and Innovation at the Brazilian Synchrotron Light Laboratory. <i>Synchrotron Radiation News</i> , 2007 , 20, 13-18	0.6	
98	Alloying mechanisms for epitaxial nanocrystals. <i>Physical Review Letters</i> , 2007 , 98, 165901	7.4	33
97	Polarization-selective excitation of nitrogen vacancy centers in diamond. <i>Physical Review B</i> , 2007 , 76,	3.3	102
96	Microstrip resonator for microwaves with controllable polarization. <i>Applied Physics Letters</i> , 2007 , 91, 204103	3.4	14
95	Equilibrium Distributions and the Nanostructure Diagram for Epitaxial Quantum Dots. <i>Journal of Computational and Theoretical Nanoscience</i> , 2007 , 4, 335-347	0.3	5
94	Absorptive and dispersive optical responses of excitons in a single quantum dot. <i>Applied Physics Letters</i> , 2006 , 89, 123124	3.4	17

93	X-ray diffraction mapping of strain fields and chemical composition of SiGe:Si(001) quantum dot molecules. <i>Physical Review B</i> , 2006 , 73,	3.3	11
92	Landé tensor in semiconductor nanostructures. <i>Physical Review Letters</i> , 2006 , 97, 236402	7.4	48
91	X-ray study of atomic ordering in self-assembled Ge islands grown on Si(001). <i>Physical Review B</i> , 2005 , 72,	3.3	39
90	Elastic energy mapping of epitaxial nanocrystals. <i>Applied Physics A: Materials Science and Processing</i> , 2005 , 80, 1211-1214	2.6	14
89	Optical properties of type-I and II quantum dots. <i>Brazilian Journal of Physics</i> , 2004 , 34, 555-559	1.2	3
88	Annealing of phosphorus-doped Ge islands on Si(001). <i>Journal of Applied Physics</i> , 2004 , 95, 1562-1567	2.5	9
87	Anisotropy of the Raman spectra of nanographite ribbons. <i>Physical Review Letters</i> , 2004 , 93, 047403	7.4	177
86	Dissipative dynamics of spins in quantum dots. <i>Physical Review B</i> , 2004 , 70,	3.3	12
85	Magneto-optics from type-II single quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2004 , 1, 543-546		1
84	Aharonov-Bohm signature for neutral polarized excitons in type-II quantum dot ensembles. <i>Physical Review Letters</i> , 2004 , 92, 126402	7.4	118
83	Transport signatures of correlated disorder in a two-dimensional electron gas. <i>Europhysics Letters</i> , 2003 , 61, 674-680	1.6	5
82	g-factor engineering and control in self-assembled quantum dots. <i>Applied Physics A: Materials Science and Processing</i> , 2003 , 77, 725-729	2.6	27
81	Ordered arrays of rare-earth silicide nanowires on Si(001). <i>Journal of Crystal Growth</i> , 2003 , 251, 657-661	1.6	48
80	3D composition of epitaxial nanocrystals by anomalous X-ray diffraction: observation of a Si-rich core in Ge domes on Si(100). <i>Physical Review Letters</i> , 2003 , 91, 176101	7.4	154
79	Influence of phosphine on Ge/Si(001) island growth by chemical vapor deposition. <i>Journal of Applied Physics</i> , 2003 , 94, 4215-4224	2.5	13
78	Controlling alloy composition of InAsP self-assembled quantum dots embedded in GaAs. <i>Journal of Applied Physics</i> , 2003 , 94, 3051-3056	2.5	7
77	Equilibrium model of bimodal distributions of epitaxial island growth. <i>Physical Review Letters</i> , 2003 , 90, 146101	7.4	68
76	Size and Shape of Epitaxial Nanostructures 2003 , 81-93		2

75	Epitaxial Growth of Strained Nanocrystals. <i>Physica Status Solidi (B): Basic Research</i> , 2002 , 230, 443-450	1.3	4
74	Nanoscience and Nanotechnology Research at the Brazilian National Synchrotron Laboratory (LNLS). <i>Physica Status Solidi (B): Basic Research</i> , 2002 , 232, 24-31	1.3	1
73	Growth and evolution of epitaxial erbium disilicide nanowires on Si (001). <i>Applied Physics A: Materials Science and Processing</i> , 2002 , 75, 353-361	2.6	32
72	Transport signatures for correlated disorder in self-assembled InAs quantum dots on GaAs. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002 , 12, 591-594	3	
71	Micro-photoluminescence of self-assembled quantum dots in the presence of an electron gas. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002 , 12, 872-875	3	10
70	Effect of phosphorus on island formation. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002 , 13, 974-977	3	3
69	Spin splitting of the electron ground states of InAs quantum dots. <i>Applied Physics Letters</i> , 2002 , 80, 4229-4231	3.4	46
68	Optical and structural properties of InAsP ternary self-assembled quantum dots embedded in GaAs. <i>Applied Physics Letters</i> , 2002 , 81, 2953-2955	3.4	21
67	Charging dynamics in vertically aligned InAs quantum dots. <i>Materials Science and Technology</i> , 2002 , 18, 725-728	1.5	6
66	Anomalous X-Ray Scattering On Self-Assembled Islands: Direct Evaluation Of Composition Profile, Strain Relaxation, And Elastic Energy. <i>Materials Research Society Symposia Proceedings</i> , 2002 , 737, 35		
65	On the origin of the blueshift from type-II quantum dots emission using microphotoluminescence. <i>Applied Physics Letters</i> , 2002 , 81, 2743-2745	3.4	24
64	Direct evaluation of composition profile, strain relaxation, and elastic energy of Ge:Si(001) self-assembled islands by anomalous x-ray scattering. <i>Physical Review B</i> , 2002 , 66,	3.3	91
63	Effect of phosphorus on Ge/Si(001) island formation. <i>Applied Physics Letters</i> , 2001 , 78, 2220-2222	3.4	11
62	Seeding of InP islands on InAs quantum dot templates. <i>Journal of Applied Physics</i> , 2001 , 89, 6548-6550	2.5	10
61	Luminescence quenching in InAs quantum dots. <i>Applied Physics Letters</i> , 2001 , 78, 2946-2948	3.4	36
60	Magnetic field dependence of the metal-insulator transition in Ga[Al]As-heterostructures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000 , 6, 264-267	3	1
59	Self-assembled growth of epitaxial erbium disilicide nanowires on silicon (001). <i>Applied Physics Letters</i> , 2000 , 76, 4004-4006	3.4	239
58	An optical study of self-assembled In _x Ga _{1-x} As/GaAs quantum dots embedded in a two-dimensional electron gas. <i>Journal of Applied Physics</i> , 2000 , 87, 7994-7998	2.5	8

57	The incommensurate nature of epitaxial titanium disilicide islands on Si(001). <i>Surface Science</i> , 2000 , 457, 147-156	1.8	28
56	Thermodynamics of the size and shape of nanocrystals: epitaxial Ge on Si(001). <i>Annual Review of Physical Chemistry</i> , 2000 , 51, 527-51	15.7	55
55	Coulomb-coupling in vertically aligned self-assembled InAs quantum dots. <i>Nanotechnology</i> , 1999 , 10, 14-18	3.4	20
54	Storage of electrons and holes in self-assembled InAs quantum dots. <i>Applied Physics Letters</i> , 1999 , 74, 1839-1841	3.4	42
53	Rehybridization of electronic structure in compressed two-dimensional quantum dot superlattices. <i>Physical Review B</i> , 1999 , 59, 1633-1636	3.3	63
52	Equilibrium size distributions of clusters during strained epitaxial growth. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999 , 67, 31-38	3.1	11
51	Transport properties of two-dimensional electron gases in Ga[Al]As heterostructures containing InAs self-assembled quantum dots. <i>Microelectronic Engineering</i> , 1999 , 47, 73-75	2.5	8
50	Electronic structure of nanometer-size quantum dots and quantum rings. <i>Microelectronic Engineering</i> , 1999 , 47, 95-99	2.5	23
49	Evolution of Ge islands on Si(001) during annealing. <i>Journal of Applied Physics</i> , 1999 , 85, 1159-1171	2.5	221
48	Titanium disilicide nanostructures: two phases and their surfaces. <i>Surface Science</i> , 1999 , 431, 116-127	1.8	27
47	The dynamics of tunneling into self-assembled InAs dots. <i>Applied Physics Letters</i> , 1999 , 74, 2486-2488	3.4	94
46	Chemical Thermodynamics of the Size and Shape of Strained Ge Nanocrystals Grown on Si(001). <i>Accounts of Chemical Research</i> , 1999 , 32, 425-433	24.3	26
45	Metal-Insulator Transition in a Disordered Two-Dimensional Electron Gas in GaAs-AlGaAs at Zero Magnetic Field. <i>Physical Review Letters</i> , 1999 , 82, 996-999	7.4	63
44	Individual and Collective Electronic Properties of Ag Nanocrystals. <i>Journal of Physical Chemistry B</i> , 1999 , 103, 10341-10347	3.4	124
43	Dome-to-pyramid transition induced by alloying of Ge islands on Si(001). <i>Applied Physics A: Materials Science and Processing</i> , 1998 , 67, 727-730	2.6	87
42	TEM study of InAs self-assembled quantum dots in GaAs. <i>Thin Solid Films</i> , 1998 , 336, 38-41	2.2	1
41	Interband absorption on self-assembled InAs quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 1998 , 2, 23-27	3	7
40	Field dependent carrier dynamics and charged excitons in InAs self-assembled quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 1998 , 2, 627-631	3	7

39	Electronic coupling effects in self-assembled InAs quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 1998 , 2, 704-708	3	25
38	Fine structure in the spectrum of the few-electron ground states of self-assembled quantum dots. <i>Physica B: Condensed Matter</i> , 1998 , 249-251, 257-261	2.8	10
37	InAs self-assembled quantum dots as controllable scattering centers near a two-dimensional electron gas. <i>Physical Review B</i> , 1998 , 58, 1506-1511	3.3	74
36	Coulomb interactions in small charge-tunable quantum dots: A simple model. <i>Physical Review B</i> , 1998 , 58, 16221-16231	3.3	237
35	Equilibrium Shape Diagram for Strained Ge Nanocrystals on Si(001). <i>Journal of Physical Chemistry B</i> , 1998 , 102, 9605-9609	3.4	39
34	Annealing of Ge nanocrystals on Si(001) at 550°C: Metastability of huts and the stability of pyramids and domes. <i>Physical Review B</i> , 1998 , 58, 3533-3536	3.3	95
33	Shape transition of germanium nanocrystals on a silicon (001) surface from pyramids to domes. <i>Science</i> , 1998 , 279, 353-5	3.3	781
32	Photoluminescence of charged InAs self-assembled quantum dots. <i>Physical Review B</i> , 1998 , 58, 3597-3600	3.3	77
31	Size distribution of coherently strained InAs quantum dots. <i>Journal of Applied Physics</i> , 1998 , 84, 4268-4272	3.3	40
30	Single-electron charging and Coulomb interaction in InAs self-assembled quantum dot arrays. <i>Physical Review B</i> , 1997 , 55, 1568-1573	3.3	99
29	Size Quantization and Zero Dimensional Effects in Self Assembled Semiconductor Quantum Dots. <i>Japanese Journal of Applied Physics</i> , 1997 , 36, 4068-4072	1.4	19
28	Charging dynamics of InAs self-assembled quantum dots. <i>Physical Review B</i> , 1997 , 56, 3609-3612	3.3	42
27	Charged Excitons in Self-Assembled Semiconductor Quantum Dots. <i>Physical Review Letters</i> , 1997 , 79, 5282-5285	7.4	282
26	Few-electron ground states of charge-tunable self-assembled quantum dots. <i>Physical Review B</i> , 1997 , 56, 6764-6769	3.3	221
25	Size quantization effects in InAs self-assembled quantum dots. <i>Applied Physics Letters</i> , 1997 , 70, 1727-1729	3.4	76
24	Intermixing and shape changes during the formation of InAs self-assembled quantum dots. <i>Applied Physics Letters</i> , 1997 , 71, 2014-2016	3.4	528
23	Luminescence spectroscopy of InAs self-assembled quantum dots. <i>Superlattices and Microstructures</i> , 1997 , 21, 259-266	2.8	16
22	Structural and optical characterization of InAs/InGaAs self-assembled quantum dots grown on (311)B GaAs. <i>Journal of Applied Physics</i> , 1996 , 80, 3466-3470	2.5	66

21	Magnetic properties and imaging of Mn-implanted GaAs semiconductors. <i>Journal of Applied Physics</i> , 1996 , 79, 5296	2.5	48
20	Inverse Bloch oscillator: Strong terahertz-photocurrent resonances at the Bloch frequency. <i>Physical Review Letters</i> , 1996 , 76, 2973-2976	7.4	168
19	Shell structure and electron-electron interaction in self-assembled InAs quantum dots. <i>Europhysics Letters</i> , 1996 , 36, 197-202	1.6	238
18	Carrier relaxation and electronic structure in InAs self-assembled quantum dots. <i>Physical Review B</i> , 1996 , 54, 11346-11353	3.3	183
17	Excited states in InAs self-assembled quantum dots 1996 , 2694, 185		2
16	Limits and Properties of Size Quantization Effects in InAs Self Assembled Quantum Dots. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 452, 275		3
15	Photon assisted transport through semiconductor quantum structures in intense terahertz electric fields. <i>Physica B: Condensed Matter</i> , 1996 , 227, 367-372	2.8	6
14	Magneto-optical properties of InAs monolayers and InyAl1-yAs self-assembled quantum dots in Ga(Al)As matrices. <i>Physica B: Condensed Matter</i> , 1996 , 227, 378-383	2.8	9
13	Three-Dimensional Carrier Confinement in Strain-Induced Self-Assembled Quantum Dots. <i>MRS Bulletin</i> , 1996 , 21, 50-54	3.2	71
12	Magnetoluminescence studies of InyAl1-yAs self-assembled quantum dots in AlxGa1-xAs matrices. <i>Physical Review B</i> , 1996 , 53, 16458-16461	3.3	61
11	Imaging and Spectroscopy of Single InAs Self-Assembled Quantum Dots using Ballistic Electron Emission Microscopy. <i>Physical Review Letters</i> , 1996 , 77, 5268-5271	7.4	79
10	Strong Terahertz-Photocurrent Resonances in Miniband Superlattices at the Bloch Frequency 1996 , 135-138		
9	Assembly of submicrometre ferromagnets in gallium arsenide semiconductors. <i>Nature</i> , 1995 , 377, 707-710	10.4	76
8	Electrical conductivity of LiIO_3 acid type crystals at 1 kHz. <i>Solid State Communications</i> , 1995 , 93, 1013-1017	10.7	8
7	DX-center energy level dependence on silicon doping concentration in $\text{Al}_{0.3}\text{Ga}_{0.7}\text{As}$. <i>Journal of Electronic Materials</i> , 1995 , 24, 907-912	1.9	1
6	Electron and hole energy levels in InAs self-assembled quantum dots. <i>Applied Physics Letters</i> , 1995 , 66, 1767-1769	3.4	188
5	Growth and Capacitance Spectroscopy of Self Assembled Quantum Dots. <i>Materials Research Society Symposia Proceedings</i> , 1995 , 417, 221		
4	Photoluminescence measurements of complex defects in Si-doped $\text{Al}_{0.3}\text{Ga}_{0.7}\text{As}$. <i>Journal of Applied Physics</i> , 1994 , 76, 8051-8054	2.5	5

3	The diffuse behavior of the ferroelectric transition in poly(vinylidene fluoride-trifluoroethylene) copolymers. <i>Journal of Polymer Science, Part B: Polymer Physics</i> , 1994 , 32, 953-959	2.6	13
2	The effect of the planar doping on the electrical transport properties at the Al:n-GaAs(100) interface: Ultrahigh effective doping. <i>Journal of Applied Physics</i> , 1993 , 73, 820-823	2.5	13
1	InAs/InGaAs self-assembled quantum dots grown on (311)B GaAs by molecular beam epitaxy		5